## ECE 320 - Final (pt 1) - Name

Semiconductors \& Diodes

1) Load Lines: Assume the VI characteristics for the diode is as shown in the graph. Draw the load line for the follosing circuit and determine Ix and Vx.

| Load Line | Vx | Ix |
| :---: | :---: | :---: |
| show on graph |  |  |


2) Nonlinear equations: Diode circuit

Assume the VI characteristics for the diodes shown below are

$$
V_{d}=0.052 \ln \left(10^{8} \cdot I_{d}+1\right) \quad I_{d}=10^{-8} \cdot\left(\exp \left(\frac{V_{d}}{0.052}\right)-1\right)
$$

Write N equations to solve for N unknonws: $\{\mathrm{V} 1, \mathrm{~V} 2, \mathrm{~V} 3, \mathrm{~V} 4, \mathrm{Id} 1, \mathrm{Id} 2, \mathrm{Id} 3\}$.

- Note: you do not need to solve.
- $\mathrm{R}=1000+100 *$ (your birth month) + (birth date). For example, May 14th gives 1514 Ohms.


3) Ideal Silicon Diodes. Assume the diodes in this circuit are ideal silicon diodes:

- $\mathrm{Vd}=0.7 \mathrm{~V} \quad \mathrm{Id}>0$
- $\mathrm{Id}=0 \quad \mathrm{Vd}<0.7 \mathrm{~V}$
- $\mathrm{R}=1000+100^{*}$ (your birth month) + (birth date). For example, May 14th gives 1514 Ohms.

| R | V1 | V2 | V3 |
| :---: | :---: | :---: | :---: |
| $1000+100^{*}$ mo + day |  |  |  |
|  |  |  |  |


4) AC to DC: Analysis: Determine V1 and V2 (both DC and AC) for the following AC to DC converter

| R | V 1 |  | V 2 |  |
| :---: | :---: | :---: | :---: | :---: |
|  | DC | AC | DC | AC |
|  |  |  |  |  |


5) Max/Min: Analysis: Determine currents I1..I6. Assume

- Ideal silicon diodes $(\mathrm{Vf}=0.7 \mathrm{~V})$
- $\mathrm{R}=1000+100^{*}$ (your birth month) + (birth date $)$

| R | I1 | I2 | I3 | I4 | I5 | I6 |
| :--- | :--- | :--- | :--- | :--- | :--- | :--- |
|  |  |  |  |  |  |  |
|  |  |  |  |  |  |  |



## ECE 320 - Final (pt 2) - Name

Transistors and Mosfets
6) Determine the current gain, $\beta$. Also draw the load line and determine the operating point when Vin $=5 \mathrm{~V}$

| R <br> $1000+100^{*}$ Mo + Day | Current Gain <br> hfe $=$ beta | Load Line | Vce | Ic |
| :---: | :---: | :---: | :---: | :---: |
|  |  | show on graph |  |  |
|  |  |  |  |  |


7) H-Bridge: Assume

- $\mathrm{R}=1000+100^{*}$ (birth month) + (birth day). May 14th would ive 1514 Ohms
- Ideal silicon transistors $(\mathrm{Vbe}=0.7 \mathrm{~V}, \mathrm{Vce}(\mathrm{sat})=0.2 \mathrm{~V}, \beta=100)$

Determine the currents for voltages for the following H bridge.

| R | I1 | I2 | I3 | V4 | V5 |
| :---: | :---: | :---: | :---: | :---: | :---: |
| $1000+100^{*}$ Mo + Day |  |  |  |  |  |
|  |  |  |  |  |  |


8) Schmitt Trigger: For the following Schmitt trigger, determine

- The voltage at V1 where V2 goes,
- The voltage at V1 where V2 goes low, and
- Rb so that the transistor is saturated when $\mathrm{V} 2=+5 \mathrm{~V}$

Let $\mathrm{R}=1000+100^{*}$ (birth month) + (birth day)

| R |  |  |  |
| :---: | :---: | :---: | :---: |
| $1000+100^{*}$ Mo + Day | Voltage at V1 where V2 goes high | Voltage at V1 where V2 goes low | Rb (off) <br> Pick Rb so that the transistor <br> saturates |
|  |  |  |  |


9) DTL Logic: Determine the voltages and currents for the following DTL logic gage. Assume

- $\mathrm{R}=1000+100^{*}$ (your birth month) + (birth day)
- Ideal silicon diodes $(\mathrm{Vf}=0.7 \mathrm{~V})$, and
- Ideal 3904 transistors $(\mathrm{Vbe}=0.7 \mathrm{~V}, \mathrm{Vce}(\mathrm{sat})=0.2 \mathrm{~V}, \beta=100)$

| R | V 1 | I 2 | V 3 | I 4 | V 5 |
| :---: | :---: | :---: | :---: | :---: | :---: |
|  |  |  |  |  |  |
|  |  |  |  |  |  |


10) MOSFET Load Line: For the following MOSFET circuit

- Determine the transconductance gain, kn,
- Draw the load line, and
- Determine $\{\mathrm{Vds}$, Ids $\}$ when $\mathrm{Vg}=5 \mathrm{~V}$

| kn <br> transconductance gain | Load Line | Ids | Vds | Operating Region <br> off / active / ohmic |
| :---: | :---: | :---: | :---: | :---: |
|  | show on graph |  |  |  |
|  |  |  |  |  |



